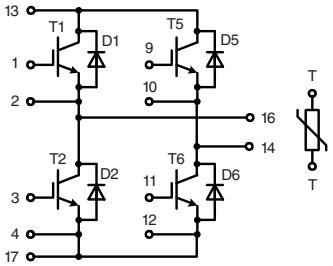
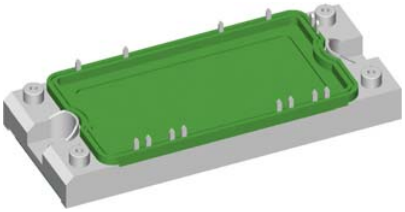
IGBT Modules
H-Bridge

Short Circuit SOA Capability
Square RBSOA

I_{C25} = 72 A
V_{CES} = 600 V
$V_{CE(sat)\,typ.}$ = 1.9 V

Type	NTC - Option
MKI 50-06 A7	without NTC
MKI 50-06 A7T	with NTC





Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy parallelling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate

Advantages

- space savings
- reduced protection circuits
- package designed for wave soldering

Typical Applications

- motor control
  - DC motor armature winding
  - DC motor excitation winding
  - synchronous motor excitation winding
- supply of transformer primary winding
  - power supplies
  - welding
  - X-ray
  - UPS
  - battery charger

IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	T_{VJ} = 25°C to 150°C	600	V
V_{GES}		± 20	V
I_{C25}	T_C = 25°C	72	A
I_{C80}	T_C = 80°C	50	A
RBSOA	V_{GE} = ±15 V; R_G = 22 Ω; T_{VJ} = 125°C Clamped inductive load; L = 100 µH	I_{CM} = 100 $V_{CEK} \le V_{CES}$	A
t_{SC} (SCSOA)	V_{CE} = V_{CES}; V_{GE} = ±15 V; R_G = 22 Ω; T_{VJ} = 125°C non-repetitive	10	µs
P_{tot}	T_C = 25°C	225	W

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
$V_{CE(sat)}$	I_C = 50 A; V_{GE} = 15 V; T_{VJ} = 25°C		1.9	2.4	V
	T_{VJ} = 125°C		2.2		V
$V_{GE(th)}$	I_C = 1 mA; V_{GE} = V_{CE}	4.5		6.5	V
I_{CES}	V_{CE} = V_{CES}; V_{GE} = 0 V; T_{VJ} = 25°C			0.6	mA
	T_{VJ} = 125°C		0.7		mA
I_{GES}	V_{CE} = 0 V; V_{GE} = ± 20 V			200	nA
$t_{d(on)}$	Inductive load, T_{VJ} = 125°C		50		ns
t_r	V_{CE} = 300 V; I_C = 50 A		60		ns
$t_{d(off)}$	V_{GE} = ±15 V; R_G = 22 Ω		300		ns
t_f			30		ns
E_{on}			2.3		mJ
E_{off}			1.7		mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz		2800		pF
Q_{Gon}	V_{CE} = 300V; V_{GE} = 15 V; I_C = 50 A		120		nC
R_{thJC}	(per IGBT)			0.55	K/W

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	T_C = 25°C	72	A
I_{F80}	T_C = 80°C	45	A

Symbol	Conditions	Characteristic Values min.	typ.	max.	
V_F	I_F = 50 A; V_{GE} = 0 V; T_{VJ} = 25°C		1.6	1.8	V
	T_{VJ} = 125°C		1.3		V
I_{RM}	I_F = 30 A; di_F/dt = -500 A/µs; T_{VJ} = 125°C		25		A
t_{rr}	V_R = 300 V; V_{GE} = 0 V		90		ns
R_{thJC}	(per diode)			1.19	K/W

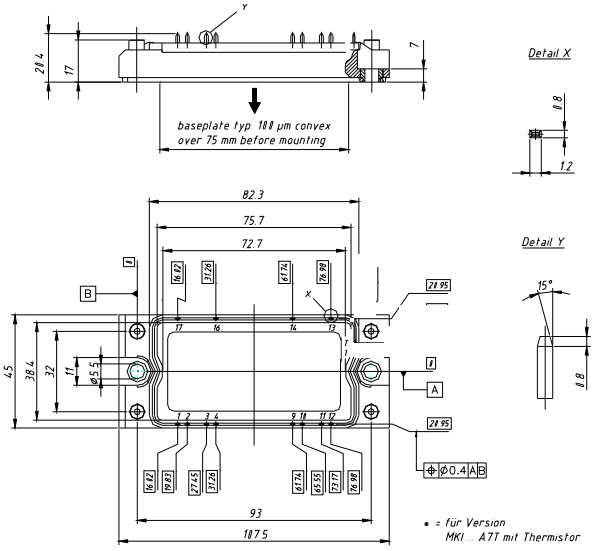
Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+150	°C
T_{stg}		-40...+125	°C
V_{ISOL}	I_{ISOL} ≤ 1 mA; 50/60 Hz	2500	V~
M_d	Mounting torque (M5)	2.7 - 3.3	Nm

Symbol	Conditions	Characteristic Values min.	typ.	max.	
$R_{pin-chip}$			5		mΩ
d_S	Creepage distance on surface	6			mm
d_A	Strike distance in air	6			mm
R_{thCH}	with heatsink compound		0.02		K/W
Weight			180		g

Temperature Sensor NTC (MKI ... A7T version only)

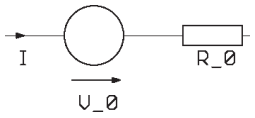
Symbol	Conditions	Characteristic Values min.	typ.	max.	
R_{25}	T = 25°C	4.75	5.0	5.25	kΩ
$B_{25/50}$			3375		K



Dimensions in mm (1 mm = 0.0394")

Equivalent Circuits for Simulation

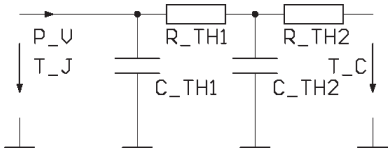
Conduction



IGBT (typ. at V_{GE} = 15 V; T_J = 125°C)
V_0 = 0.82 V; R_0 = 28 mΩ

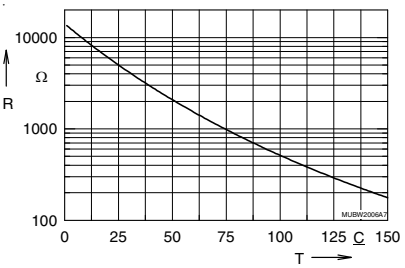
Free Wheeling Diode (typ. at T_J = 125°C)
V_0 = 0.89 V; R_0 = 8 mΩ

Thermal Response



IGBT (typ.)
C_{th1} = 0.201 J/K; R_{th1} = 0.42 K/W
C_{th2} = 1.252 J/K; R_{th2} = 0.131 K/W

Free Wheeling Diode (typ.)
C_{th1} = 0.116 J/K; R_{th1} = 0.973 K/W
C_{th2} = 0.88 J/K; R_{th2} = 0.277 K/W



Typ. thermistor resistance versus temperature

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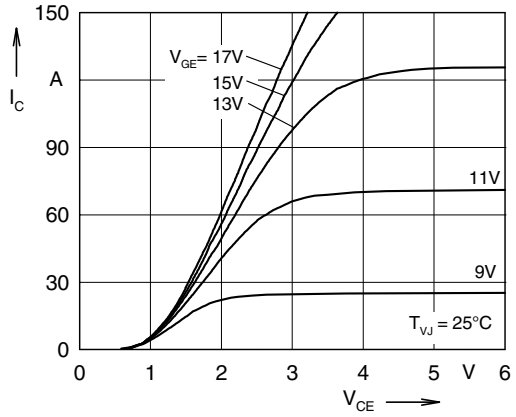

Fig. 1 Typ. output characteristics

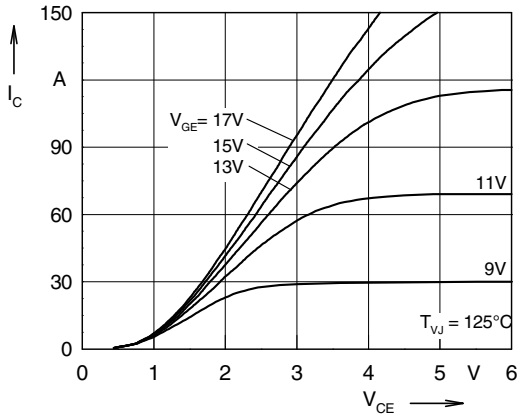

Fig. 2 Typ. output characteristics

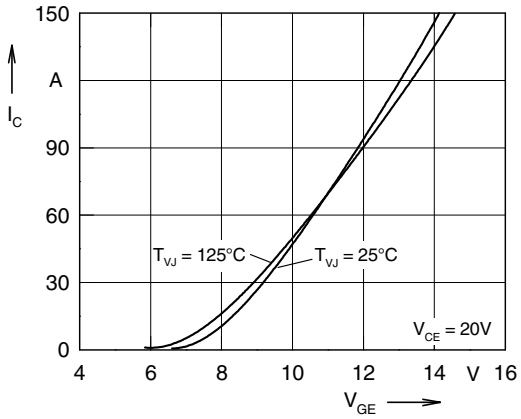

Fig. 3 Typ. transfer characteristics

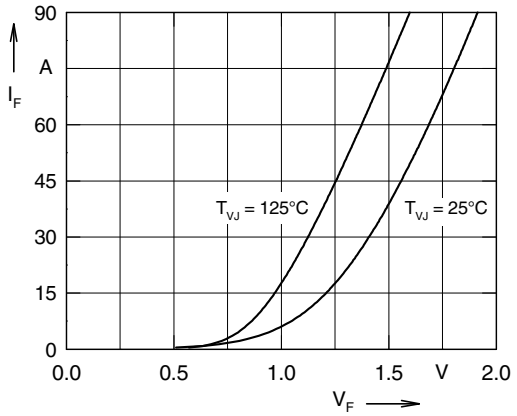

Fig. 4 Typ. forward characteristics of free wheeling diode

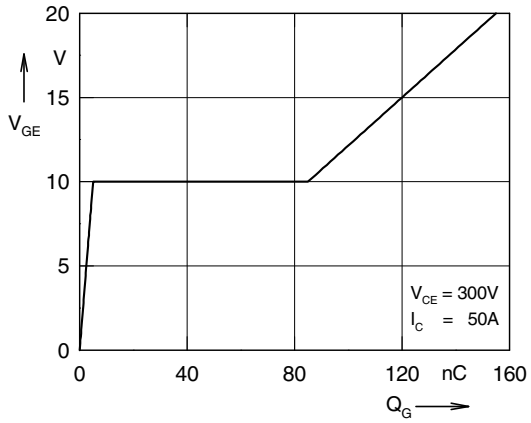

Fig. 5 Typ. turn on gate charge

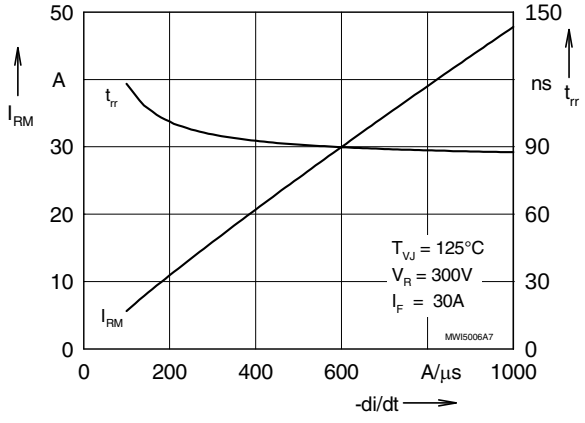

Fig. 6 Typ. turn off characteristics of free wheeling diode

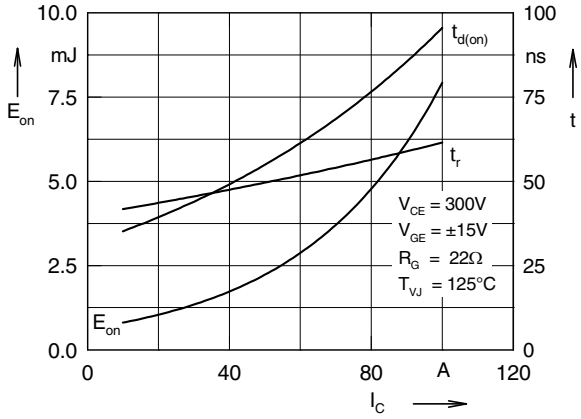

Fig. 7 Typ. turn on energy and switching times versus collector current

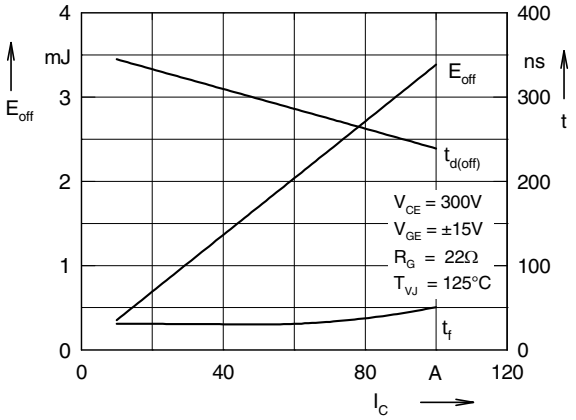

Fig. 8 Typ. turn off energy and switching times versus collector current

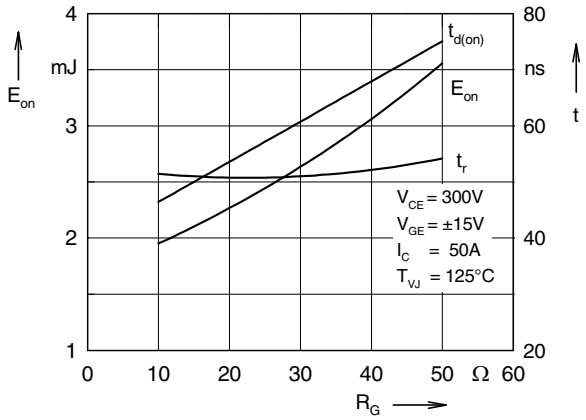

Fig. 9 Typ. turn on energy and switching times versus gate resistor

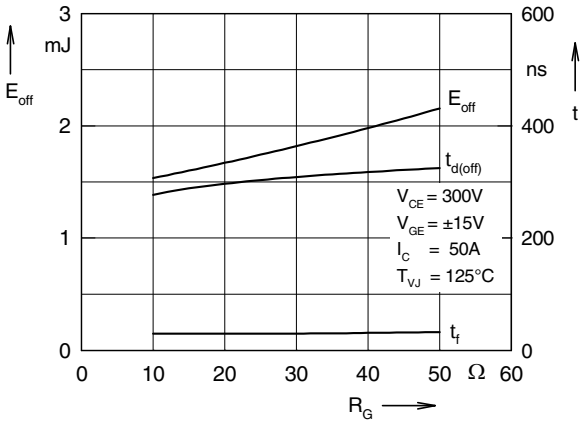

Fig.10 Typ. turn off energy and switching times versus gate resistor

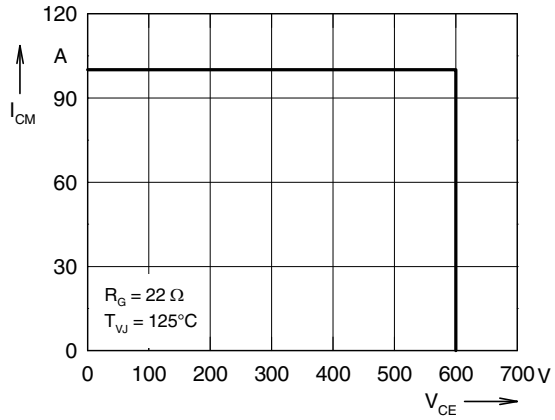

Fig. 11 Reverse biased safe operating area RBSOA

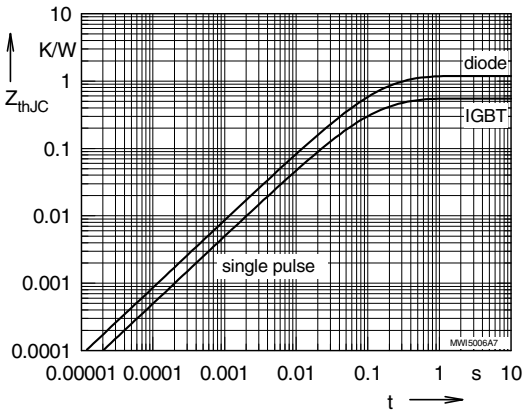

Fig. 12 Typ. transient thermal impedance